

TO-92L Plastic-Encapsulate Transistors

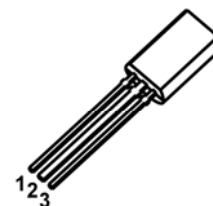
2SA935 TRANSISTOR (PNP)

FEATURES

- General Purpose Switching Application

TO – 92L

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-0.7	A
P _C	Collector Power Dissipation	750	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -50μA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-2mA, I _B =0	-80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} =-3V, I _C =-100mA	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.4	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			20	pF
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA		100		MHz

CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390